

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE				Atty. Docket No. GB 010121		Serial No.	
				Applicant Mark A. GAJDA			
				Filing Date CONCURRENTLY		Group 2823	
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)							
U.S. PATENT DOCUMENTS							
Ex. Int.		Document Number	Date	Name	Class	Sub-class	Filing Date If Approp.
WLL	AA	6 0 8 7 2 2 4	7/11/2000	Luo	438	270	
	AB						
	AC						
	AD						
	AE						
	AF						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-class	Trans. Yes No
WLL	AG	W 0 0 2 1 5 2 5 4	2/21/2002	PCT	H01L	21/336	
	AH						
	AI						
	AJ						
	AK						
OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)							
WLL	AL	VISPSD' 2000 Proceedings, pages 181-184					
	AM						
	AN						
Examiner <u>WLL</u> Date Considered <u>9/5/03</u>							
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.							

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Sheet 1 of 1

Form PTO-1449 COMMERCE (REV. 7-80)		U.S. DEPARTMENT OF PATENT AND TRADEMARK OFFICE		Atty. Docket No. GB 010121		Serial No. 10/197,651		
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant MARK A. GAJDA				
				Filing 7/17/02		Group 2842 2823		
U.S. PATENT DOCUMENTS								
Ex. Int.		Document Number	Date	Name	Class	Sub-class	Filing Date If Approp.	
	AA							
	AB							
	AC							
	AD							
	AE							
	AF							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Sub-class	Trans.	
							Yes No	
WLL	AC	1 9 5 0 7 1 4 6 A	11/1/96	GERMANY	H01L	29/78		X
WLL	AH	W 0 0 1 6 5 6 0 8	7/9/01	PCT (WORLD)	H01L	29/78	X	
	AI							
	AJ							
	AK							
OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)								
WLL	AL	Juang et al: "A process simplification scheme for fabricating self-aligned silicided trench-gate power MOSFETs" solid state Electronics, Elsevier Science Publishers, vol. 45, no. 1, January 2001, pages 169-172						
WLL	AM	Norstrom et al: "Formation of CoSi2 and TiSi2 on narrow poly-Si lines" Microelectronic engineering, vol. 14, no. 3-4, September 1991, pages 327-339						
	AN							
Examiner <i>WLL</i>				Date Considered 9/03/03				
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